

TISP8200HDM BUFFERED P-GATE SCR DUAL TISP8201HDM BUFFERED N-GATE SCR DUAL

COMPLEMENTARY BUFFERED-GATE SCRS FOR DUAL POLARITY SLIC OVERVOLTAGE PROTECTION

TISP820xHDM Overvoltage Protectors

High Performance Protection for SLICs with +ve & -ve Battery Supplies

TISP8200HDM Negative Overvoltage Protector

- Wide -20 to -110 V Programming Range
- Low +15 mA Max. Gate Triggering Current
- High -150 mA Min. Holding Current

TISP8201HDM Positive Overvoltage Protector

- Wide +20 to +110 V Programming Range

- Low -15 mA Max. Gate Triggering Current

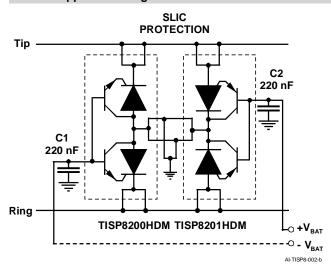
- +20 mA Min. Holding Current

Rated for International Surge Wave Shapes

Wave Shape	Standard	I _{PPSM} A
2/10	GR-1089-CORE	500
10/700	ITU-T K.20/21/45	150
10/1000	GR-1089-CORE	100

UL Recognized Component

Circuit Application Diagram





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Additional Information

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Agency Recognition

Description				
UL	File Number: E215609			

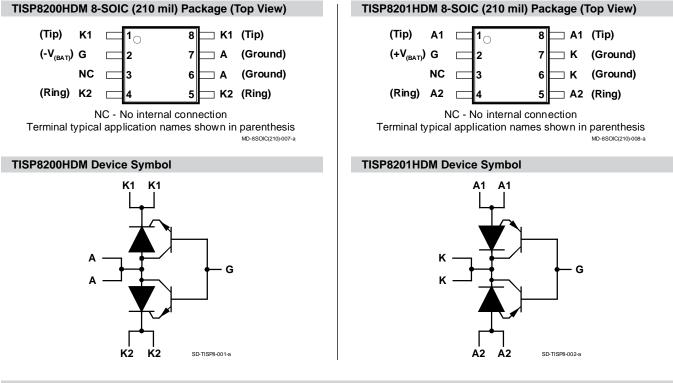
Description

The TISP8200HDM/TISP8201HDM combination has been designed to protect dual polarity supply rail monolithic SLICs (Subscriber Line Interface Circuits) against overvoltages on the telephone line caused by lightning, a.c. power contact and induction. Protection against negative overvoltages is given by the TISP8200HDM. Protection against positive overvoltages is given by the TISP8201HDM. Both parts are in 8-SOIC (210 mil) surface mount packages.

The TISP8200HDM has an array of two buffered P-gate SCRs with a common anode connection. Each SCR cathode and gate has a separate terminal connection. The NPN buffer transistors reduce the gate supply current. In use, the cathodes of the TISP8200HDM SCRs are connected to the two conductors of the POTS line. The gates are connected to the appropriate negative voltage battery feed of the SLIC driving the line conductor pair, so that the TISP8200HDM protection voltage tracks the SLIC negative supply voltage. The anode of the TISP8200HDM is connected to the SLIC common. Negative overvoltages are initially clipped close to the SLIC negative supply by emitter follower action of the NPN buffer transistor. If sufficient clipping current flows, the SCR will regenerate and switch into a low voltage on-state condition. As the overvoltage subsides the high holding current of the SCR helps prevent d.c. latchup.

The TISP8201HDM has an array of two buffered N-gate SCRs with a common cathode connection. Each SCR anode and gate has a separate terminal connection. The PNP buffer transistors reduce the gate supply current. In use, the anodes of the TISP8201HDM SCRs are connected to the two conductors of the POTS line. The gates are connected to the appropriate positive voltage battery feed of the SLIC driving that line pair, so that the TISP8201HDM protection voltage tracks the SLIC positive supply voltage. The cathode of the TISP8201HDM is connected to the SLIC common. Positive overvoltages are initially clipped close to the SLIC positive supply by emitter follower action of the PNP buffer transistor. If sufficient clipping current flows the SCR will regenerate and switch into a low voltage on-state condition. As the overvoltage subsides the SLIC pulls the conductor voltage down to its normal negative value and this commutates the conducting SCR into a reverse biased condition.

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How to Order

Device	Package	Carrier	Order As	Marking Code	Standard Quantity
TISP8200HDM	8-SOIC (210 mil)	Embossed Tape Reeled	TISP8200HDMR-S	8200H	2000
TISP8201HDM	8-SOIC (210 mil)	Embossed Tape Reeled	TISP8201HDMR-S	8201H	2000

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TISP8200HDM Absolute Maximum Ratings, T_A = 25 °C (Unless Otherwise Noted)

Rating	Symbol	Value	Unit
Repetitive peak off-state voltage, V _{GK} = 0	V _{DRM}	-120	V
Repetitive peak reverse voltage, V _{GA} = -70 V	V _{RRM}	120	
Non-repetitive peak impulse curr ent (see Notes 1, 2 and 3)			
2/10 μ s (Telcordia GR-1089-CORE, 2/10 μ s voltage wave shape)		-500	
5/310 μ s (ITU-T K.44, 10/700 μ s voltage wave shape used in K.20/21/45)	IPPSM	-150	A
10/1000 μ s (Telcordia GR-1089-CORE, 10/1000 μ s voltage wave shape)		-100	
Non-repetitive peak on-s tate current, 50/60 Hz (see Notes 1, 2, 3 and 4)			
10 ms		60	
1s		14	
7 s	ITSM	7	A
900 s		3.5	
Junction temperatur e	Т _Ј	-55 to +150	°C
Storage temperature range	T _{stg}	-65 to +150	°C

NOTES: 1. Initially the device must be in thermal equilibrium with T_J = 25 °C. The surge may be repeated after the device returns to its initial conditions.

2. These non-repetitive rated currents are peak values. The rated current values may be applied to any cathode-anode ter minal pair.

3. Rated currents only apply if pins 1 & 8 (K1,Tip) are connected together, pins 4 & 5 (K2, Ring) are connected together and pins 6 & 7 (A. Ground) are connected together.

4. These non-repetitive rated terminal currents are for the TISP8200HDM and TISP8201HDM together. Device (A)-terminal positive current values are conducted by the TISP8201HDM and (K)-terminal negative current values by the TISP8200HDM.

TISP8201HDM Absolute Maximum Ratings, T_A = 25 °C (Unless Otherwise Noted)

Rating	Symbol	Value	Unit
Repetitive peak off-state voltage, V _{GA} = 0	V _{DRM}	120	V
Repetitive peak reverse voltage, V _{GK} = 70 V	V _{RRM}	-120	
Non-repetitive peak impulse curr ent (see Notes 5, 6 and 7)			
2/10 μ s (Telcordia GR-1089-CORE, 2/10 μ s voltage wave shape)		500	
5/310 μ s (ITU-T K.44, 10/700 μ s voltage wave shape used in K.20/21/45)	I _{PPSM}	150	A
10/1000 μ s (Telcordia GR-1089-CORE, 10/1000 μ s voltage wave shape)		100	
Non-repetitive peak on-s tate current, 50/60 Hz (see Notes 5, 6, 7 and 8)			
10 ms		60	
1 s		14	•
7 s	ITSM	7	A
900 s		3.5	
Junction temperatur e	TJ	-55 to +150	°C
Storage temperature range	T _{stg}	-65 to +150	°C

NOTES: 5. Initially the device must be in thermal equilibrium with T_J = 25 °C. The surge may be repeated after the device returns to its initial conditions.

6. These non-repetitive rated currents are peak values. The rated current values may be applied to any cathode-anode ter minal pair.

7. Rated currents only apply if pins 1 & 8 (A1, Tip) are connected together, pins 4 & 5 (A2, Ring) are connected together and pins 6 & 7 (K, Ground) are connected together.

8. These non-repetitive rated terminal currents are for the TISP8200HDM and TISP8201HDM together. Device (A)-terminal positive current values are conducted by the TISP8201HDM and (K)-terminal negative current values by the TISP8200HDM.

Recommended Operating Conditions				
See Figure 3	Min	Тур	Мах	Unit
C1, C2 Gate decoupling capacitor		220		nF

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TISP8200HDM Electrical Characteristics, T_A = 25 °C (Unless Otherwise Noted)

	Parameter	Test Conditions		Min	Тур	Max	Unit
I _{DRM}	Repetitive peak off-state current	$V_{\rm D} = V_{\rm DRM}, V_{\rm GK} = 0$				-5	μA
I _{RRM}	Repetitive peak reverse current	$V_{R} = V_{RRM}, V_{GA} = -70 V$				5	μA
V _(BO)	Breakover voltage	dv/dt = -250 V/ms, R_{SOURCE} = 300 Ω , V_{GA} = -80 V				-82	V
V _(BO)	Impulse breakover voltage	dv/dt \leq -1000 V/ μ s, Linear voltage ramp, Maximum ramp value = -500 V di/dt = -20 A/ μ s, Linear current ramp, Maximum ramp value = -10 A V _{GA} = -80 V				-90	v
Ι _Η	Holding current	$(I_{K}) I_{T} = -1 \text{ A}, \text{ di/dt} = 1 \text{ A/ms}, V_{GA} = -80 \text{ V}$		-150			mA
I _{GT}	Gate trigger current	$(I_K) I_T = -5 \text{ A}, t_{p(g)} \ge 20 \ \mu \text{s}, V_{GA} = -80 \text{ V}$				15	mA
Co	Off-state capacitance	$I_{t} = 1 MHz V_{s} = 1 V rms$ (jate open	V _D = -2 V = -50 V			65 30	pF

TISP8201HDM Electrical Characteristics, T_A = 25 °C (Unless Otherwise Noted)

	Parameter	Test Conditions		Min	Тур	Max	Unit
I _{DRM}	Repetitive peak off-state cur rent	$V_{\rm D} = V_{\rm DRM}, V_{\rm GA} = 0$				5	μA
I _{RRM}	Repetitive peak reverse current	$V_{\rm R} = V_{\rm RRM}, V_{\rm GK} = 70 \text{ V}$				-5	μA
V _(BO)	Breakover voltage	dv/dt = 250 V/ms, R_{SOURCE} = 300 Ω , V_{GK} = 80 V				82	V
V _(BO)	Impulse breakover voltage	$dv/dt \le 1000 V/\mu$ s, Linear voltage ramp, Maximum ramp value = 500 V di/dt = 20 A/µs, Linear current ramp, Maximum ramp value = 10 A V _{GK} = 80 V				90	v
Ι _Η	Holding current	$(I_A) I_T = 1 \text{ A}, \text{ di/dt} = -1 \text{ A/ms}, V_{GK} = 80 \text{ V}$		20			mA
I _{GT}	Gate trigger current	$(I_A) I_T = 5 \text{ A}, t_{p(g)} \ge 20 \ \mu \text{s}, V_{GK} = 80 \text{ V}$				-15	mA
C _O	Off-state capacitance	f = 1 MHz, V _d = 1 V rms, Gate open	V _D = 2 V V _D = 50 V			50 30	pF

Thermal Characteristics

	Parameter	Test Conditions	Min	Тур	Мах	Unit
R_{\thetaJA}	Junction to ambient thermal resistance	EIA/JESD51-7 PCB, EIA/JESD51-2 Environment, P _{TOT} = 4 W (See Note 9)		55		°C/W

NOTE 9. EIA/JESD51-7 high effective thermal conductivity test board (multi-layer) connected with 0.6 mm printed wiring track widths.

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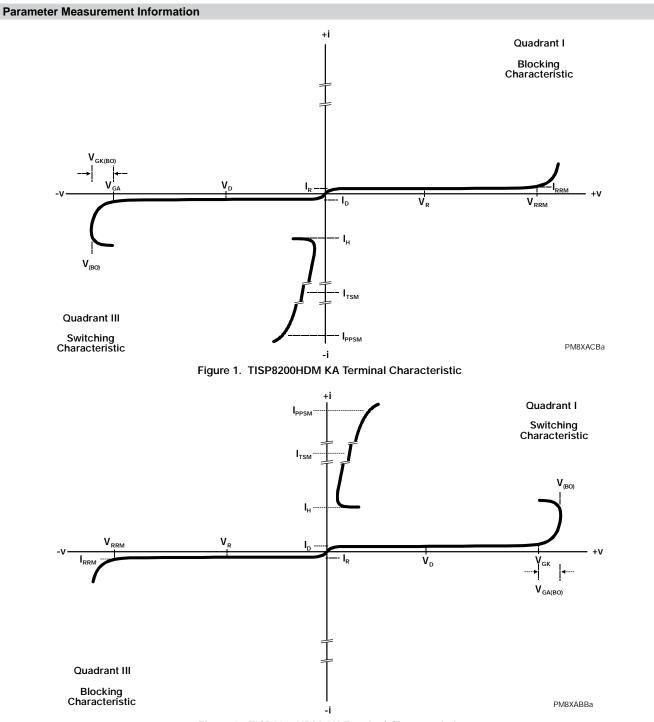


Figure 2. TISP8201HDM AK Terminal Characteristic

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AI-TISP8-001-b

Applications Information

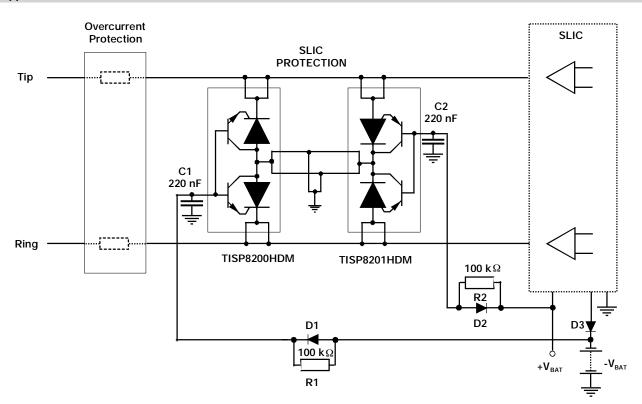


Figure 3. Typical Application Circuit

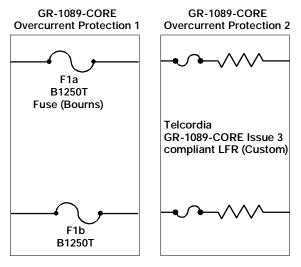


Figure 4. Typical Overcurrent Protection

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